MOSFETs Silicon N-Channel MOS (DTMOSIV)

# TK16A60W

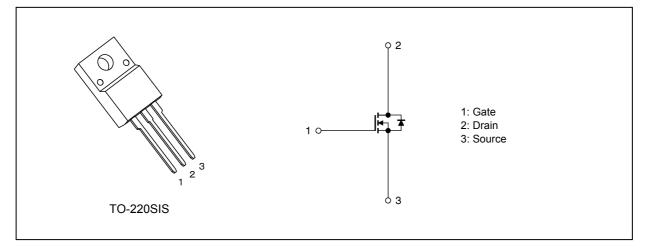
### 1. Applications

Switching Voltage Regulators

#### 2. Features

- (1) Low drain-source on-resistance:  $R_{DS(ON)} = 0.16 \Omega$  (typ.) by used to Super Junction Structure : DTMOS
- (2) Easy to control Gate switching
- (3) Enhancement mode:  $V_{th}$  = 2.7 to 3.7 V ( $V_{DS}$  = 10 V,  $I_D$  = 0.79 mA)

### 3. Packaging and Internal Circuit



#### 4. Absolute Maximum Ratings (Note) ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Rating	Unit	
Drain-source voltage		V <sub>DSS</sub>	600	V
Gate-source voltage		V <sub>GSS</sub>	±30	
Drain current (DC)	(Note 1)	Ι <sub>D</sub>	15.8	Α
Drain current (pulsed)	(Note 1)	I <sub>DP</sub>	63.2	
Power dissipation (T <sub>c</sub> = 25	5°C)	PD	40	W
Single-pulse avalanche energy	(Note 2)	E <sub>AS</sub>	231	mJ
Avalanche current		I <sub>AR</sub>	4.0	Α
Reverse drain current (DC)	(Note 1)	I <sub>DR</sub>	15.8	
Reverse drain current (pulsed)	(Note 1)	I <sub>DRP</sub>	63.2	
Channel temperature		T <sub>ch</sub>	150	°C
Storage temperature		T <sub>stg</sub>	-55 to 150	
Isolation voltage (RMS) (t = 1.0	) s)	V <sub>ISO(RMS)</sub>	2000	V
Mounting torque		TOR	0.6	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production

#### 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R <sub>th(ch-c)</sub>	3.13	°C/W
Channel-to-ambient thermal resistance	R <sub>th(ch-a)</sub>	62.5	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V<sub>DD</sub> = 90 V, T<sub>ch</sub> = 25°C (initial), L = 25.3 mH, R<sub>G</sub> = 25  $\Omega$ , I<sub>AR</sub> = 4.0 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

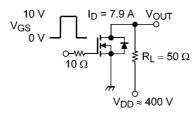
#### 6. Electrical Characteristics

### 6.1. Static Characteristics (Ta = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS}$ = ±30 V, $V_{DS}$ = 0 V	_	_	±1	μA
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V	_	_	10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	600	_	—	V
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.79 mA	2.7	_	3.7	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 7.9 A		0.16	0.19	Ω

### 6.2. Dynamic Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 300 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	1350	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	]		4	_	
Output capacitance	C <sub>oss</sub>	1		35	_	
Effective output capacitance	C <sub>o(er)</sub>	$V_{DS}$ = 0 to 400 V, $V_{GS}$ = 0 V		55	_	
Gate resistance	r <sub>g</sub>	V <sub>DS</sub> = OPEN, f = 1 MHz		6	_	Ω
Switching time (rise time)	t <sub>r</sub>	See Figure 6.2.1		25	_	ns
Switching time (turn-on time)	t <sub>on</sub>	]		50	_	
Switching time (fall time)	t <sub>f</sub>	]		5	_	
Switching time (turn-off time)	t <sub>off</sub>	]		100		
MOSFET dv/dt ruggedness	dv/dt	V <sub>DD</sub> = 0 to 400 V, I <sub>D</sub> = 7.9 A	50	_	_	V/ns



Duty  $\leq$  1%,  $t_W =$  10  $\mu s$ 

#### Fig. 6.2.1 Switching Time Test Circuit

## 6.3. Gate Charge Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V},  V_{GS} \text{ = } 10 \text{ V},  \text{I}_{D} \text{ = } 15.8 \text{ A}$	_	38	—	nC
Gate-source charge 1	Q <sub>gs1</sub>		_	9	—	
Gate-drain charge	Q <sub>gd</sub>		_	16	_	

#### 6.4. Source-Drain Characteristics (Ta = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V <sub>DSF</sub>	I <sub>DR</sub> = 15.8 A, V <sub>GS</sub> = 0 V			-1.7	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = 7.9 A, V <sub>GS</sub> = 0 V	_	280	_	ns
Reverse recovery charge	Q <sub>rr</sub>	-dI <sub>DR</sub> /dt = 100 A/μs		2.9	_	μC
Peak reverse recovery current	۱ <sub>rr</sub>			23	_	А
Diode dv/dt ruggedness	dv/dt	$I_{DR}$ = 7.9 A, $V_{GS}$ = 0 V, $V_{DD}$ = 400 V	15			V/ns

## 7. Marking (Note)

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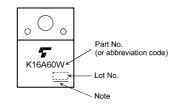
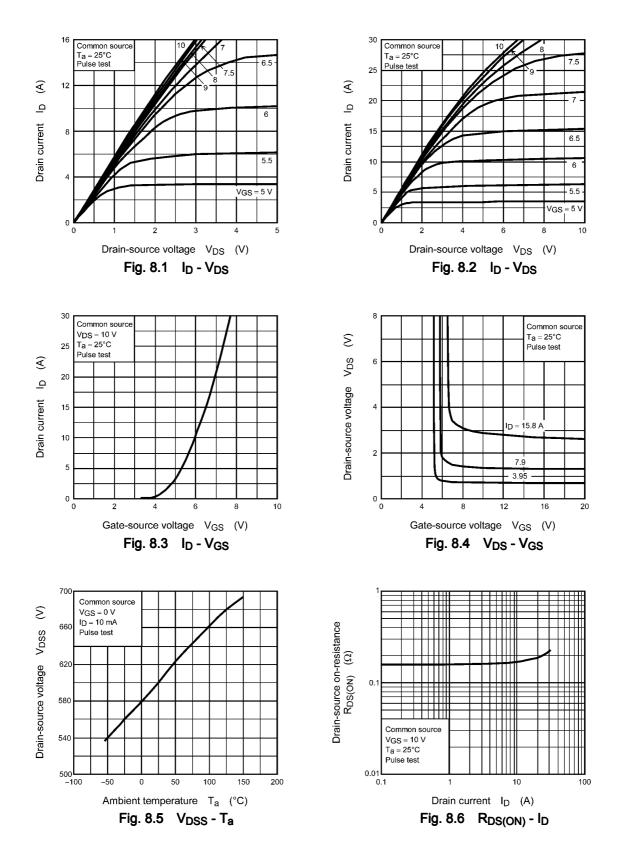
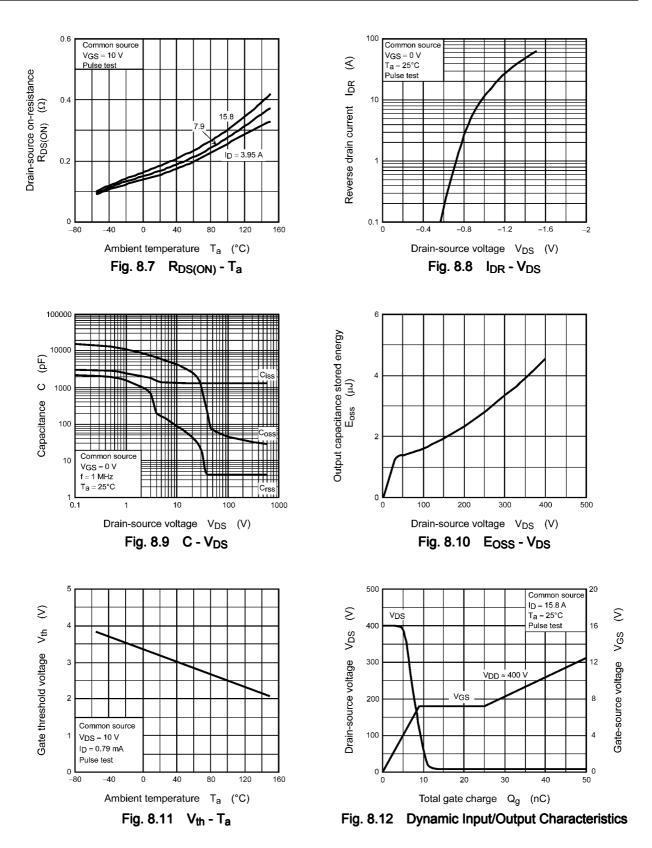


Fig. 7.1 Marking

 Note: A line under a Lot No. identifies the indication of product Labels. Not underlined: [[Pb]]/INCLUDES > MCV Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]
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### 8. Characteristics Curves (Note)





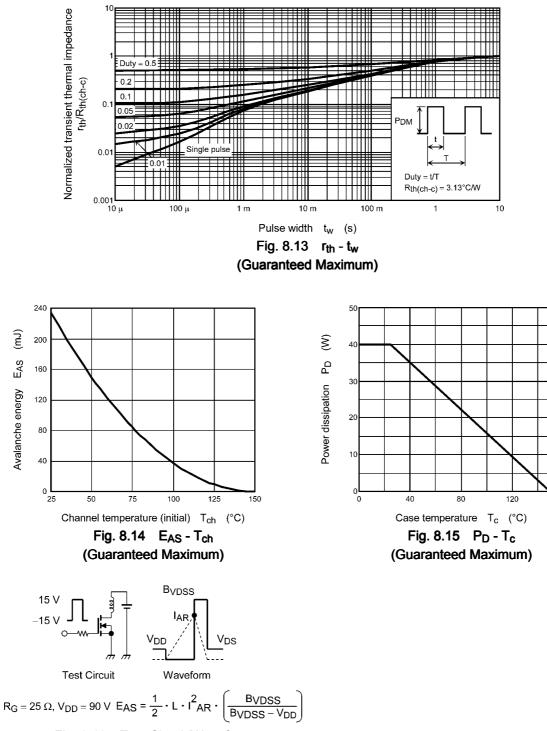
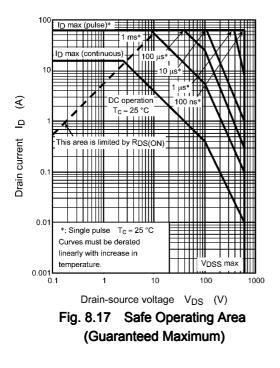


Fig. 8.16 Test Circuit/Waveform

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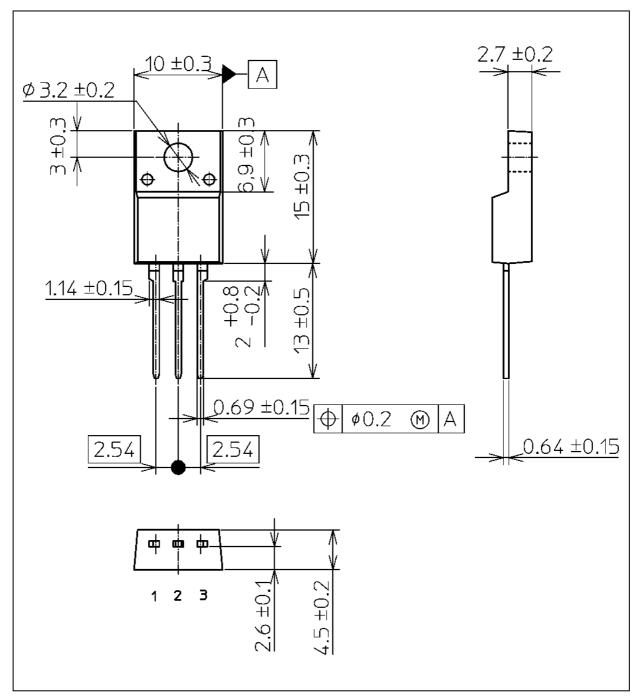


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

### Package Dimensions

TK16A60W

Unit: mm



Weight: 1.7 g (typ.)

Pac	ckage Name(s)
JEITA: SC-67	
TOSHIBA: 2-10U1S	
Nickname: TO-220SIS	

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